

Description

The SI2333-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

 $V_{DS} = -20V, I_D = -6.5A$ $R_{DS(ON)} < 28m\Omega @ V_{GS} = -4.5V$

Application

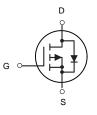
Battery protection

Load switch

Uninterruptible power supply







P-Channel MOSFET

Package Marking and Ordering Information

| Product ID | Pack | Marking | Qty(PCS) |
|------------|--------|---------|----------|
| SI2333-HXY | SOT-23 | 20P07 | 3000 |

Absolute Maximum Ratings (TA=25[°]C unless otherwise noted)

| Symbol | Parameter | Limit | Unit |
|----------------|--|------------|------|
| Vds | Drain-Source Voltage | -20 | V |
| Vgs | Gate-Source Voltage | ±12 | V |
| l _D | Drain Current-Continuous | -6.5 | A |
| Іл | Drain Current-Pulsed (Note 1) | -15 | A |
| PD | Maximum Power Dissipation | 2 | W |
| Тյ,Тѕтс | Operating Junction and Storage Temperature Range | -55 To 150 | °C |
| Reja | Thermal Resistance, Junction-to-Ambient (Note 2) | 74 | °C/W |



Electrical Characteristics (T_A=25°C unless otherwise noted)

| • | | • | | | | |
|------------------------------------|---------------------|--|-------|------|------|----|
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =-250µA | - | -20 | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-20V,V _{GS} =0V | - | - | -1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±8V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=-250\mu A$ | -0.45 | -0.7 | -1.0 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =-4.5V, I _D =-4.1A | | | 28 | mΩ |
| | | V _{GS} =-2.5V, I _D =-3A | | | 36 | |
| Forward Transconductance | g fs | V _{DS} =-5V,I _D =-3.5A | - | 8.5 | - | S |
| Dynamic Characteristics (Note4) | · | | • | • | | • |
| Input Capacitance | C _{lss} | (1 - 4)(1)(-0)(| - | 980 | - | PF |
| Output Capacitance | C _{oss} | – V _{DS} =-4V,V _{GS} =0V, – F=1.0MHz | - | 450 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | 1.0ivii iz | - | 250 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 12 | - | nS |
| Turn-on Rise Time | tr | V _{DD} =-4V,I _D =-3.3A , | - | 35 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | R_{L} =-1.2 Ω , V_{GEN} =-4.5 V , R_{g} =1 Ω | - | 30 | - | nS |
| Turn-Off Fall Time | t _f | | - | 10 | - | nS |
| Total Gate Charge | Qg | | - | 7.8 | - | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =-4V,I _D =-4.1A,V _{GS} =-4.5V | - | 1.2 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 1.6 | - | nC |
| Drain-Source Diode Characteristics | | | | | - | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =-1.6A | - | - | -1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 1.6 | Α |

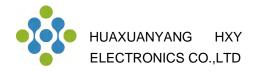
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Characteristics

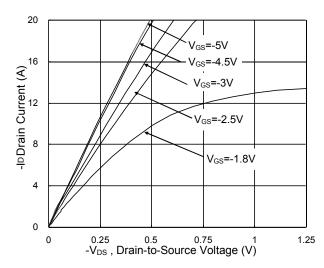


Fig.1 Typical Output Characteristics

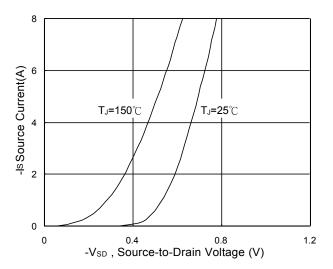


Fig.3 Forward Characteristics Of Reverse

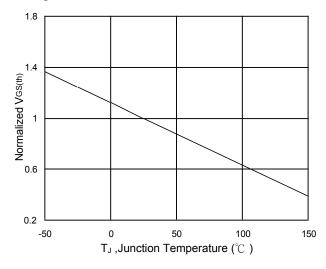


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

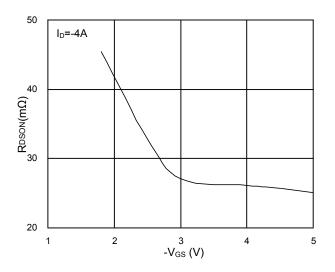


Fig.2 On-Resistance vs. Gate-Source

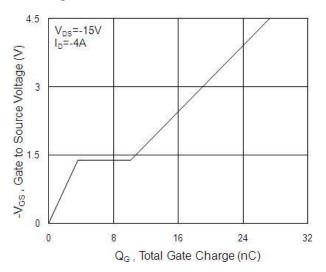


Fig.4 Gate-Charge Characteristics

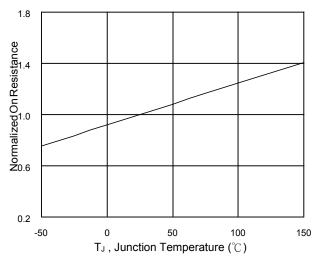
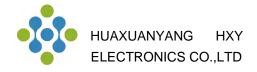
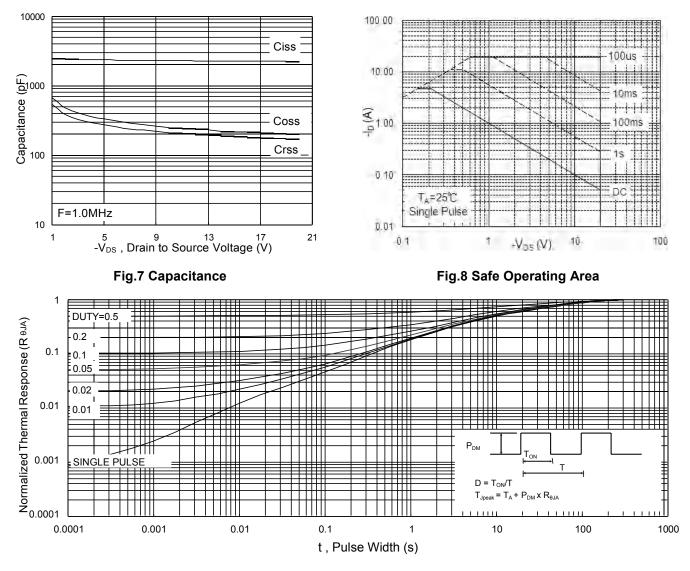


Fig.6 Normalized RDSON vs. TJ







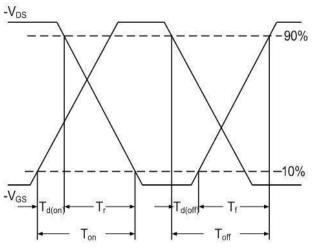


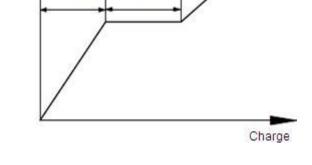
Fig.10 Switching Time Waveform

ig.3 Normalized Maximum Translent mermai impedance

-V_{GS}

4.5V

Qgs



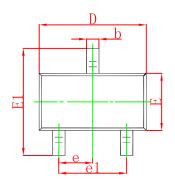
Qg

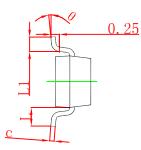
Qgd

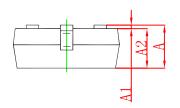




SOT-23 Package Outline Dimensions

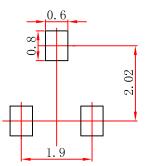






| Symbol | Dimensions In Millimeters | | Dimensions In Inches | | |
|--------|---------------------------|-------|----------------------|-------|--|
| | Min | Max | Min | Max | |
| Α | 0.900 | 1.150 | 0.035 | 0.045 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.800 | 3.000 | 0.110 | 0.118 | |
| Е | 1.200 | 1.400 | 0.047 | 0.055 | |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| e | 0.950 TYP | | 0.037 TYP | | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.550 REF | | 0.022 REF | | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 | |
| θ | 0° | 8° | 0° | 8° | |

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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